Silicon PNP Epitaxial

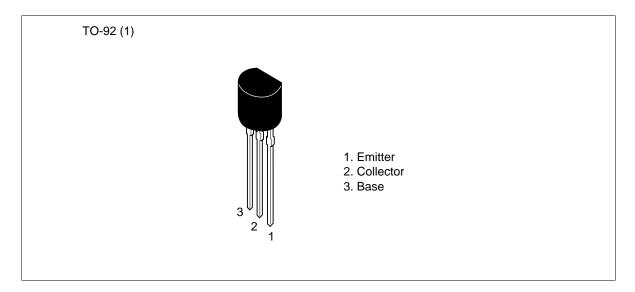
HITACHI

ADE-208-314 (Z) 1st. Edition Mar. 2001

Application

High voltage medium speed switching

Outline



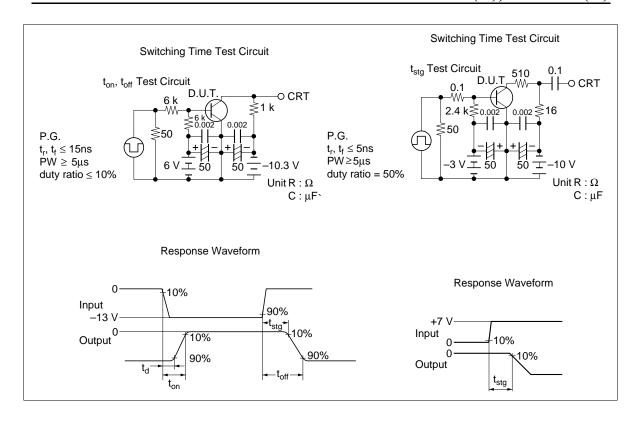


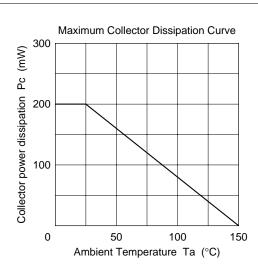
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

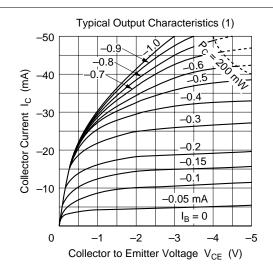
Item	Symbol	2SA778(K)	2SA778A(K)	Unit
Collector to base voltage	V_{CBO}	-150	-180	V
Collector to emitter voltage	V _{CEO}	-150	-180	V
Emitter to base voltage	V_{EBO}	- 5	– 5	V
Collector current	I _c	-50	– 50	mA
Collector power dissipation	P _c	200	200	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

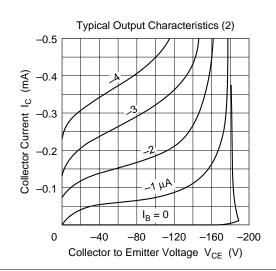
Electrical Characteristics ($Ta = 25^{\circ}C$)

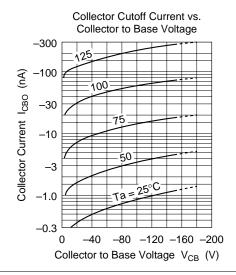
		2SA7	78(K)		2SA778A(K)				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-150	_	_	-180	_	_	V	$I_{\rm C} = -50 \ \mu A, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CER}$	-150	_	_	-180	_	_	V	$I_{C} = -50 \mu A,$ $R_{BE} = 30 k\Omega$
Collector cutoff current	I _{CBO}	_	_	-1.0	_	_	_	μΑ	$V_{CB} = -100 \text{ V}, I_{E} = 0$
		_	_	_	_	_	-1.0	μΑ	$V_{CB} = -150 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	-1.0	_	_	-1.0	μΑ	$V_{EB} = -5 \text{ V}, I_{C} = 0$
DC current transfer ratio	h_{FE}	30	100	_	40	100	200		$V_{CE} = -3 \text{ V},$ $I_E = -15 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	-0.3	-1.0	_	-0.3	-1.0	V	$I_{\rm C} = -15 \text{ mA},$ $I_{\rm B} = -1 \text{ mA}$
Base to emitter saturation voltage	$V_{\text{BE}(\text{sat})}$	_	-0.77	-1.0	_	-0.77	-1.0	V	$I_C = -15 \text{ mA},$ $I_B = -1 \text{ mA}$
Collector output capacitance	Cob	_	_	10	_	_	10	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz
Gain bandwidth product	f _T	_	50	_	_	50	_	MHz	$V_{CE} = -3 \text{ V},$ $I_{C} = -15 \text{ mA}$
Turn on time	t _{on}	_	135	_	_	135	_	ns	V _{CC} = -10.3 V
Turn off time	t _{off}	_	1.7	_	_	1.7	_	μs	$I_{\rm C} = 10 I_{\rm B1} = -10$ $I_{\rm B2} = -10 \text{ mA}$
Storage time	t _{stg}	_	_	1.0	_	_	1.0	μs	$V_{CC} = -10 \text{ V},$ $I_{C} = -17 \text{ mA}$ $I_{B1} = -1 \text{mA},$ $I_{B2} = -12 \text{ mA}$

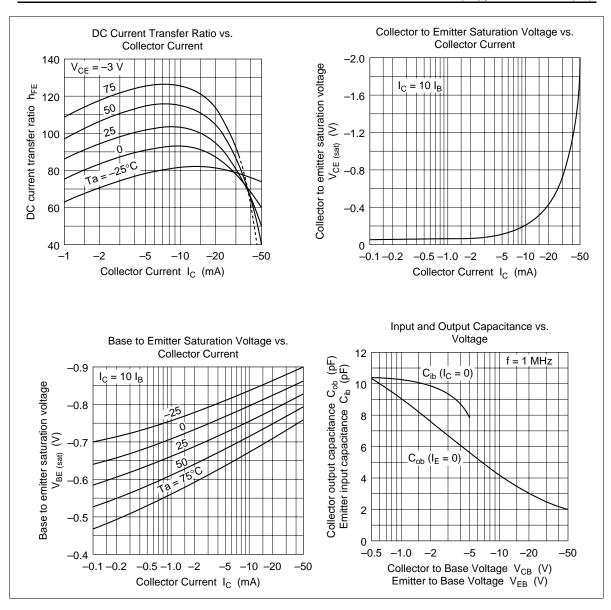


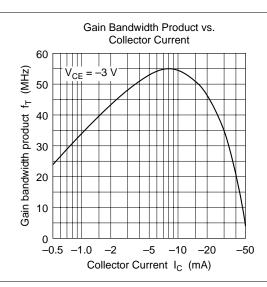


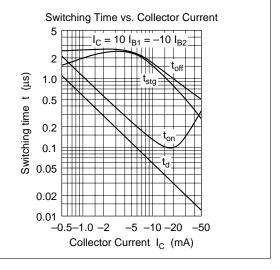




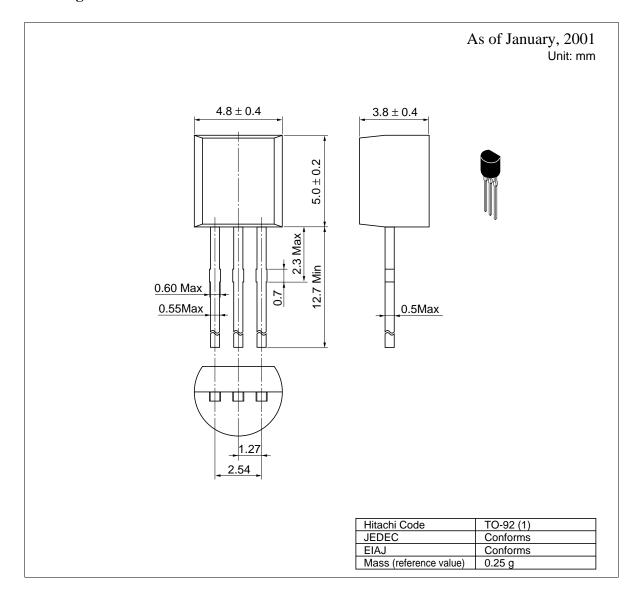








Package Dimensions



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